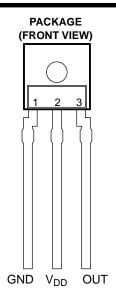


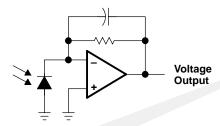
- Converts Light Intensity to Output Voltage
- Monolithic Silicon IC Containing Photodiode, Operational Amplifier, and Feedback Components
- High Sensitivity
- Single Voltage Supply Operation (2.7 V to 5.5 V)
- Low Noise (200 μVrms Typ to 1 kHz)
- Rail-to-Rail Output
- High Power-Supply Rejection (35 dB at 1 kHz)
- Compact 3-Leaded Plastic Package



### **Description**

The TSL257 is a high-sensitivity low-noise light-to-voltage optical converter that combines a photodiode and a transimpedance amplifier on a single monolithic CMOS integrated circuit. Output voltage is directly proportional to light intensity (irradiance) on the photodiode. The TSL257 has a transimpedance gain of 320 M $\Omega$ . The device has improved offset voltage stability and low power consumption and is supplied in a 3-lead clear plastic sidelooker package with an integral lens.

### **Functional Block Diagram**



### **Terminal Functions**

TERMINAL		DECORIDATION
NAME	NO.	DESCRIPTION
GND	1	Ground (substrate). All voltages are referenced to GND.
OUT	3	Output voltage
$V_{DD}$	2	Supply voltage

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## TSL257 HIGH-SENSITIVITY LIGHT-TO-VOLTAGE CONVERTER

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### Absolute Maximum Ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage, V <sub>DD</sub> (see Note 1)	6 V
Output current, I <sub>O</sub>	±10 mA
Duration of short-circuit current at (or below) 25°C	5 s
Operating free-air temperature range, T <sub>A</sub>	
Storage temperature range, T <sub>stq</sub>	–25°C to 85°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	240°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltages are with respect to GND.

### **Recommended Operating Conditions**

	MIN	MAX	UNIT
Supply voltage, $V_{DD}$	2.7	5.5	V
Operating free-air temperature, T <sub>A</sub>	0	70	°C

# Electrical Characteristics at $V_{DD}$ = 5 V, $T_A$ = 25°C, $\lambda_p$ = 470 nm, $R_L$ = 10 k $\Omega$ (unless otherwise noted) (see Notes 2 and 3)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
$V_D$	Dark voltage	E <sub>e</sub> = 0	0		15	mV	
V <sub>OM</sub>	Maximum output voltage swing	V <sub>DD</sub> = 4.5 V, No Load		4.49		.,	
		$V_{DD} = 4.5 \text{ V}, \qquad R_L = 10 \text{ k}\Omega$	4	4.2		V	
Vo	Output voltage	$E_e = 1.54 \ \mu W/cm^2$ , $\lambda_p = 470 \ nm$ , Note 5	1.6	2	2.4	V	
$\alpha_{VD}$	Temperature coefficient of dark voltage (V <sub>D</sub> )	$T_A = 0$ °C to $70$ °C		-15		μV/°C	
N <sub>e</sub>	Irradiance responsivity	$\lambda_p$ = 428 nm, see Notes 4 and 8		1.18		V/(μW/cm²)	
		$\lambda_p$ = 470 nm, see Notes 5 and 8		1.30			
		$\lambda_p$ = 565 nm, see Notes 6 and 8		1.58			
		$\lambda_p$ = 645 nm, see Notes 7 and 8		1.68			
PSRR	Power supply rejection ratio	f <sub>ac</sub> = 100 Hz, see Note 9		55		dB	
		f <sub>ac</sub> = 1 kHz, see Note 9		35		dB	
$I_{DD}$	Supply current	$E_e = 1.54 \ \mu W/cm^2$ , $\lambda_p = 470 \ nm$ , Note 5		1.9	3.5	mA	

NOTES: 2. Measured with  $R_L = 10 \text{ k}\Omega$  between output and ground.

- 3. Optical measurements are made using small-angle incident radiation from a light-emitting diode (LED) optical source.
- 4. The input irradiance is supplied by a GaN/SiC light-emitting diode with the following characteristics: peak wavelength  $\lambda_p$  = 428 nm, spectral halfwidth  $\Delta\lambda 1/2$  = 65 nm.
- 5. The input irradiance is supplied by an InGaN light-emitting diode with the following characteristics: peak wavelength  $\lambda_p$  = 470 nm, spectral halfwidth  $\Delta\lambda \frac{1}{2}$  = 35 nm.
- 6. The input irradiance is supplied by a GaP light-emitting diode with the following characteristics: peak wavelength  $\lambda_p$  = 565 nm, spectral halfwidth  $\Delta\lambda 1/2$  = 28 nm.
- 7. The input irradiance is supplied by an AlGaAs light-emitting diode with the following characteristics: peak wavelength  $\lambda_p$  = 645 nm, spectral halfwidth  $\Delta\lambda 1/2$  = 25 nm.
- 8. Irradiance responsivity is characterized over the range  $V_O = 0.1 \text{ V}$  to 4.5 V. The best-fit straight line of Output Voltage  $V_O$  versus Irradiance  $E_e$  over this range will typically have a positive extrapolated  $V_O$  value for  $E_e = 0$ .
- 9. Power supply rejection ratio PSRR is defined as 20 log  $(\Delta V_{DD}(f)/\Delta V_{O}(f))$  with  $V_{DD}(f=0)=5$  V and  $V_{O}(f=0)=2$  V.



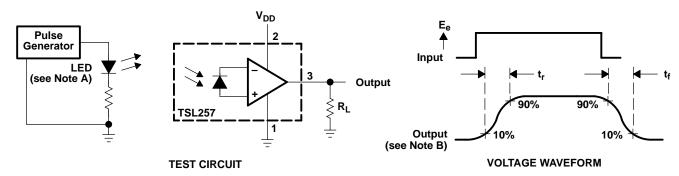
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# Switching Characteristics at V<sub>DD</sub> = 5 V, T<sub>A</sub> = 25°C, $\lambda_p$ = 470 nm, R<sub>L</sub> = 10 k $\Omega$ (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>r</sub>	Output pulse rise time, 10% to 90% of final value	See Note 10 and Figure 1		160	250	μs
t <sub>f</sub>	Output pulse fall time, 10% to 90% of final value	See Note 10 and Figure 1		150	250	μs
ts	Output settling time to 1% of final value	See Note 10 and Figure 1		330		μs
	Integrated noise voltage	$f = dc to 1 kHz$ $E_e = 0$		200		μVrms
		$f = 10 \text{ Hz}$ $E_e = 0$		6		
$V_n$	Output noise voltage, rms	$f = 100 \text{ Hz}$ $E_e = 0$		6		μV/√ <del>Hz</del> rms
		$f = 1 \text{ kHz}$ $E_e = 0$		7		

NOTE 10: Switching characteristics apply over the range  $V_0 = 0.1 \text{ V}$  to 4.5 V.

### PARAMETER MEASUREMENT INFORMATION

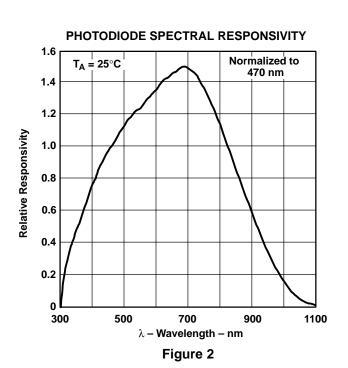


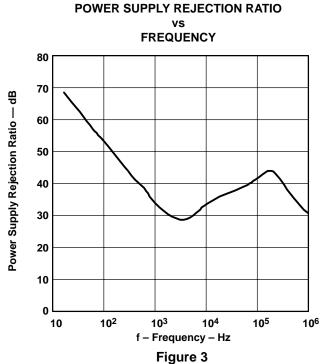
NOTES: A. The input irradiance is supplied by a pulsed InGaN light-emitting diode with the following characteristics:  $\lambda_p$  = 470 nm,  $t_r < 1 \ \mu s$ ,  $t_f < 1 \ \mu s$ .

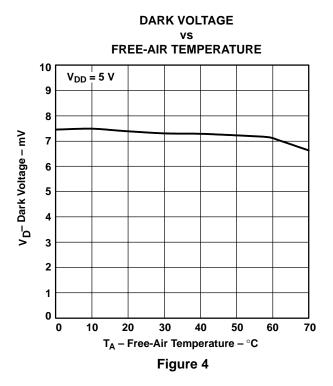
B. The output waveform is monitored on an oscilloscope with the following characteristics:  $t_r < 100$  ns,  $Z_i \ge 1$  M $\Omega$ ,  $C_i \le 20$  pF.

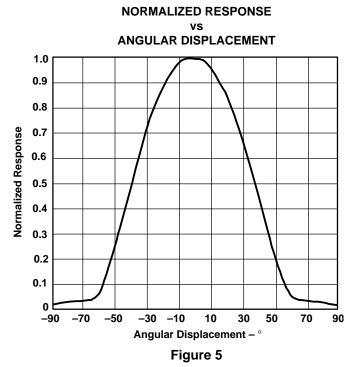
Figure 1. Switching Times

### **TYPICAL CHARACTERISTICS**











### **MECHANICAL DATA**

The TSL257 is implemented in a clear 3-leaded package with a molded focusing lens.

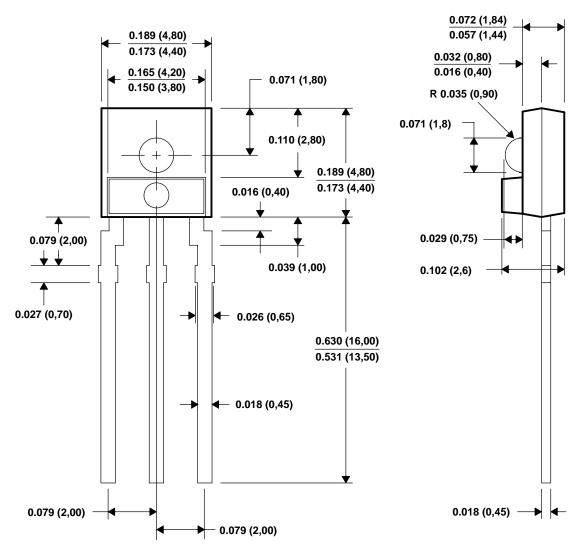


Figure 6. Package Configuration

NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. All dimensions apply before solder dip.
- D. Package body is a clear nonfilled optically transparent material
- E. Index of refraction of clear plastic is 1.55.

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